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[IXYS Corporation](#)
[DSA50C100QB](#)

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sales@integrated-circuit.com

Schottky Diode Gen ²

$$V_{RRM} = 100V$$

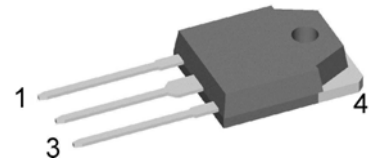
$$I_{FAV} = 2 \times 25A$$

$$V_F = 0.72V$$

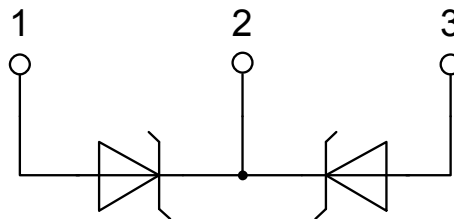
High Performance Schottky Diode
 Low Loss and Soft Recovery
 Common Cathode

Part number

DSA50C100QB



Backside: cathode



Features / Advantages:

- Very low V_f
- Extremely low switching losses
- Low I_{rm} values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

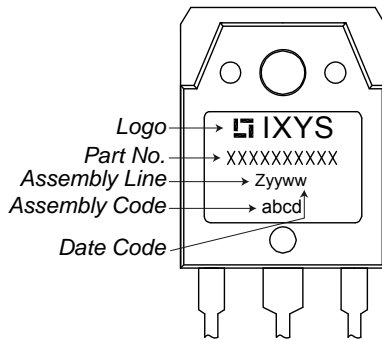
Package: TO-3P

- Industry standard outline compatible with TO-247
- RoHS compliant
- Epoxy meets UL 94V-0

Schottky				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage		$T_{VJ} = 25^{\circ}C$			100	V
V_{RRM}	max. repetitive reverse blocking voltage		$T_{VJ} = 25^{\circ}C$			100	V
I_R	reverse current, drain current	$V_R = 100\text{ V}$	$T_{VJ} = 25^{\circ}C$			450	μA
		$V_R = 100\text{ V}$	$T_{VJ} = 125^{\circ}C$			5	mA
V_F	forward voltage drop	$I_F = 25\text{ A}$	$T_{VJ} = 25^{\circ}C$			0.90	V
		$I_F = 50\text{ A}$				1.07	V
		$I_F = 25\text{ A}$	$T_{VJ} = 125^{\circ}C$			0.72	V
		$I_F = 50\text{ A}$				0.90	V
I_{FAV}	average forward current	$T_C = 155^{\circ}C$ rectangular $d = 0.5$	$T_{VJ} = 175^{\circ}C$			25	A
V_{F0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 175^{\circ}C$			0.45	V
r_F	slope resistance					7.3	m Ω
R_{thJC}	thermal resistance junction to case					0.95	K/W
R_{thCH}	thermal resistance case to heatsink				0.25		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$			160	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$	$T_{VJ} = 45^{\circ}C$			440	A
C_J	junction capacitance	$V_R = 12\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}C$			289	pF

Package TO-3P			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ¹⁾			50	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				5		g
M_D	mounting torque		0.8		1.2	Nm
F_C	mounting force with clip		20		120	N

Product Marking



Part number

- D = Diode
- S = Schottky Diode
- A = low VF
- 50 = Current Rating [A]
- C = Common Cathode
- 100 = Reverse Voltage [V]
- QB = TO-3P (3)

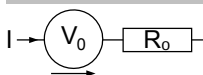
Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSA50C100QB	DSA50C100QB	Tube	30	504033

Similar Part	Package	Voltage class
DSA50C100HB	TO-247AD (3)	100
DSA60C100PB	TO-220AB (3)	100

Equivalent Circuits for Simulation

* on die level

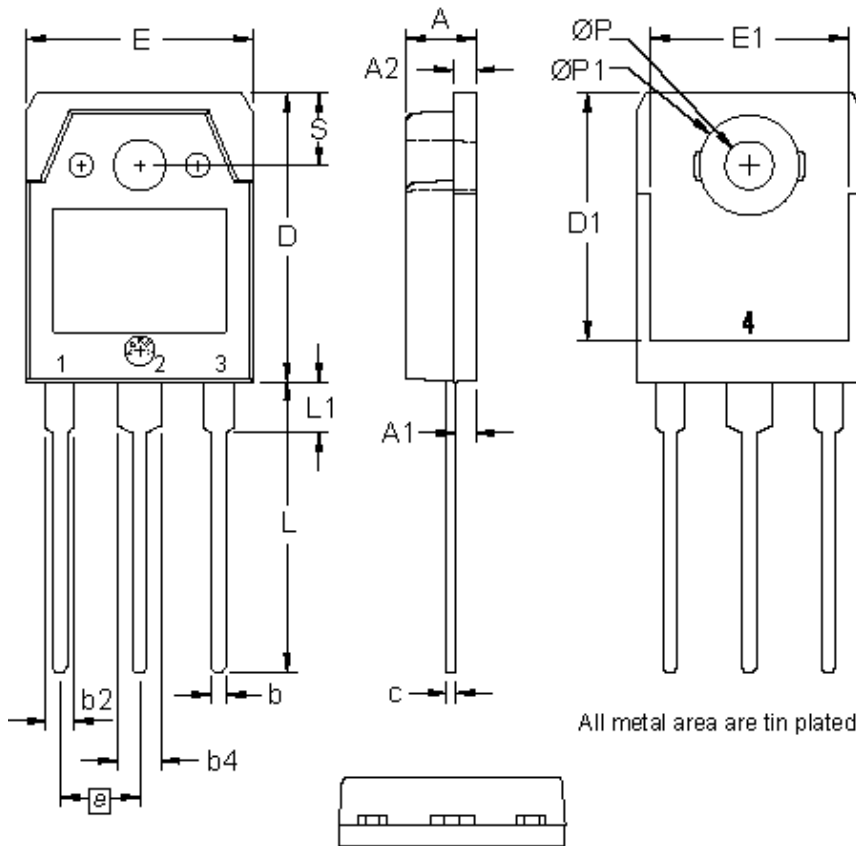
$T_{VJ} = 175\text{ °C}$



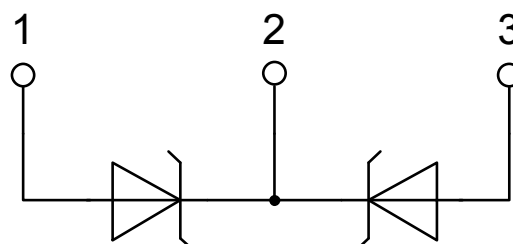
Schottky

$V_{0\ max}$	threshold voltage	0.45	V
$R_{0\ max}$	slope resistance *	4.7	mΩ

Outlines TO-3P



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.70	4.90	0.185	0.193
A1	1.30	1.50	0.051	0.059
A2	1.45	1.65	0.057	0.065
b	0.90	1.15	0.035	0.045
b2	1.90	2.20	0.075	0.087
b4	2.90	3.20	0.114	0.126
c	0.55	0.80	0.022	0.031
D	19.80	20.10	0.780	0.791
D1	16.90	17.20	0.665	0.677
E	15.50	15.80	0.610	0.622
E1	13.50	13.70	0.531	0.539
e	5.45 BSC		0.215 BSC	
L	19.80	20.20	0.780	0.795
L1	3.40	3.60	0.134	0.142
Ø P	3.20	3.40	0.126	0.134
ØP1	6.90	7.10	0.272	0.280
S	4.90	5.10	0.193	0.201



Schottky

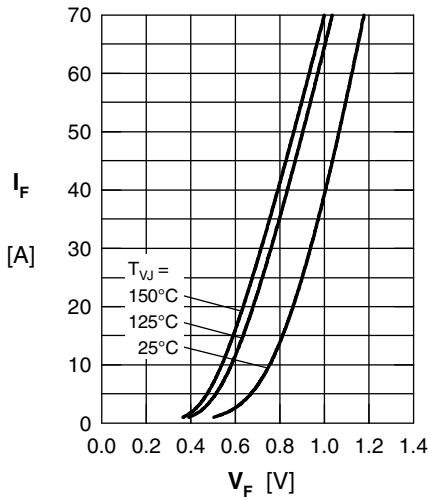


Fig. 1 Maximum forward voltage drop characteristics

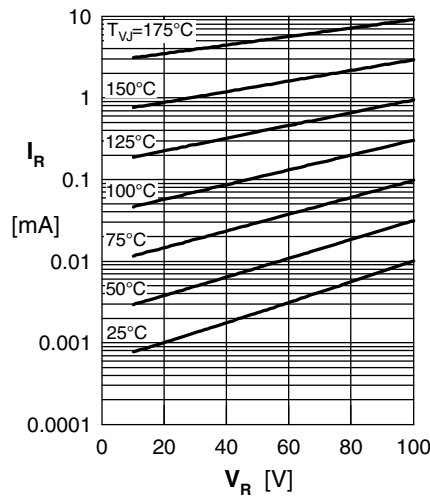


Fig. 2 Typ. reverse current I_R vs. reverse voltage V_R

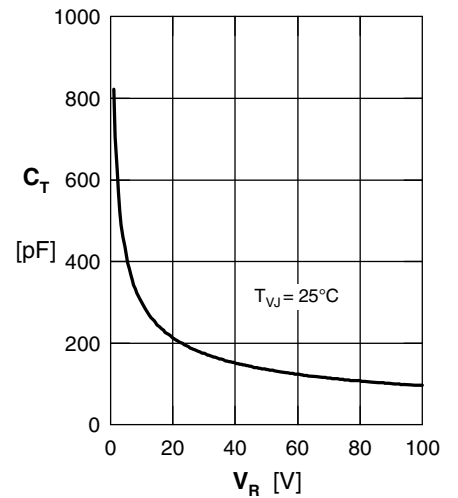


Fig. 3 Typ. junction capacitance C_T vs. reverse voltage V_R

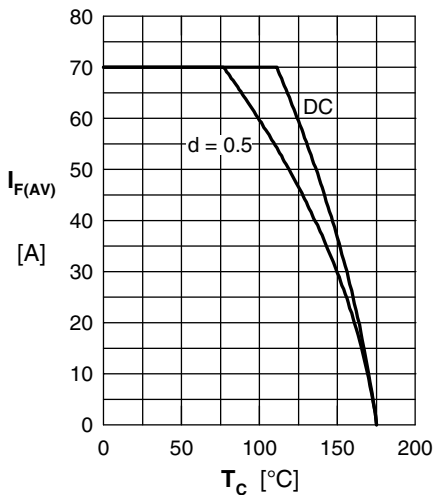


Fig. 4 Average forward current $I_{F(AV)}$ vs. case temperature T_C

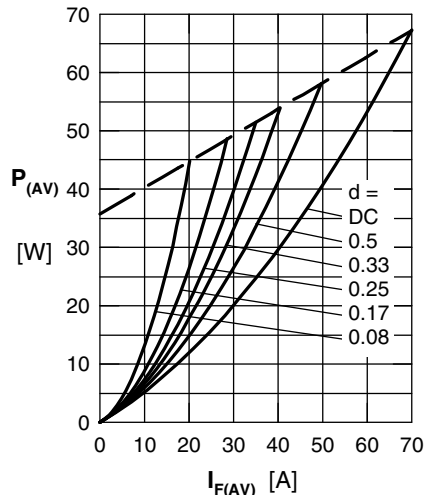


Fig. 5 Forward power loss characteristics

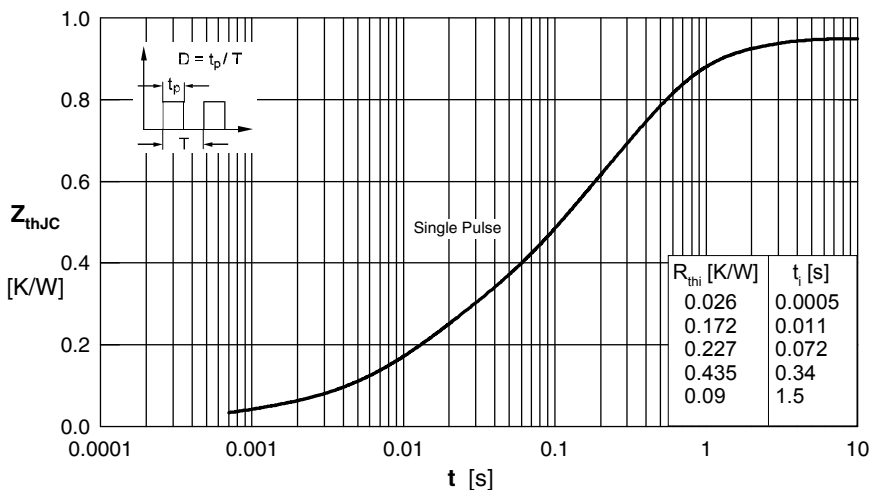


Fig. 6 Transient thermal impedance junction to case

Note: All curves are per diode